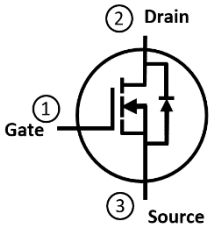
PJP75N06SA-AU

60V N-Channel Enhancement Mode MOSFET

Voltage	60 V	Current	64 A

TO-220AB-L



Features

- $R_{DS(ON)}$, V_{GS}@10V, I_D@20A<9mΩ
- $R_{DS(ON)}$, V_{GS}@4.5V, I_D@20A<17mΩ
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : TO-220AB-L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 2.0948 grams

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current(Note 3)	T_C=25°C	I_D	64	A
	T_C=100°C		46	
Pulsed Drain Current(Note 1)	T_C=25°C	I_{DM}	232	
Power Dissipation	T_C=25°C	P_D	75	W
	T_C=100°C		38	
Continuous Drain Current(Note 4)	T_A=25°C	I_D	11.5	A
	T_A=70°C		9.7	
Power Dissipation	T_A=25°C	P_D	2.4	W
	T_A=70°C		1.7	
Single Pulse Avalanche Current(Note 5)		I_{AS}	20	A
Single Pulse Avalanche Energy(Note 5)		E_{AS}	48	mJ
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55~175	°C
Thermal Resistance(Note 4)	Junction to Case	$R_{\theta JC}$	2	°C/W
	Junction to Ambient	$R_{\theta JA}$	62.5	

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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.5	2.2	3	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	-	7.2	9	mΩ
		V_{GS}=4.5V, I_D=20A	-	13	17	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V	-	-	1	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Dynamic(Note 6)						
Total Gate Charge	Q_g	V_{DS}=30V, I_D=20A, V_{GS}=10V	-	27	35	nC
Gate-Source Charge	Q_{gs}		-	7	-	
Gate-Drain Charge	Q_{gd}		-	6	-	
Input Capacitance	Ciss	V_{DS}=30V, V_{GS}=0V, f=1MHz	-	1454	1890	pF
Output Capacitance	Coss		-	616	862	
Reverse Transfer Capacitance	Crss		-	54	-	
Gate resistance	R_g	f=1MHz	-	1	-	Ω
Turn-On Delay Time	$td_{(on)}$	V_{DS}=30V, I_D=20A, V_{GS}=10V, R_G=3Ω (Note 2)	-	7.8	-	ns
Turn-On Rise Time	t_r		-	28	-	
Turn-Off Delay Time	$td_{(off)}$		-	22	-	
Turn-Off Fall Time	t_f		-	50	-	
Drain-Source Diode						
Diode Forward Current	I_S	T_C=25°C	-	-	64	A
Pulsed Diode Forward Current	I_{SM}		-	-	232	
Diode Forward Voltage	V_{SD}	I_S=20A, V_{GS}=0V	-	0.85	1.3	V
Reverse Recovery Time	Trr	V_{DD}=30V,V_{GS}=0V	-	24	-	ns
Reverse Recovery Charge	Qrr	I_S=20A,dI_S/dt=100A/us	-	9.2	-	nC

NOTES :

1. Pulse width≤100us, Duty cycle≤2%.
2. Essentially independent of operating temperature typical characteristics.
3. Chip capability with an $R_{\theta JC}$=2°C/W.
4. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance.
5. E_{AS} is calculated based on the condition of L=1mH, I_{AS}=10A, V_{DD}=30V, V_{GS}=10V. 100% test at L=0.1mH, I_{AS}=20A in production.
6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

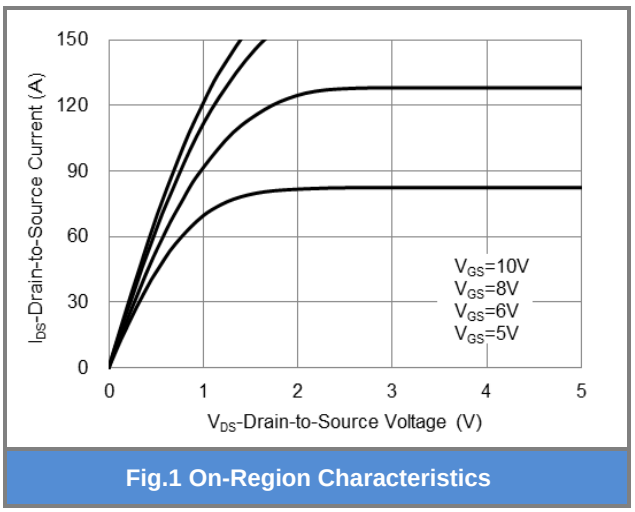

Fig.1 On-Region Characteristics

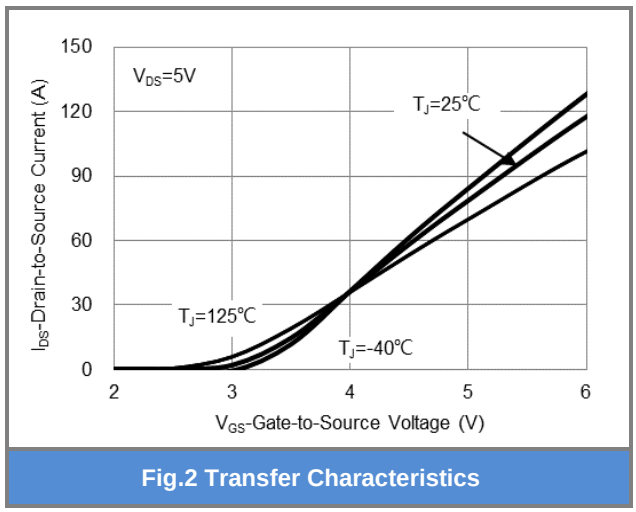

Fig.2 Transfer Characteristics

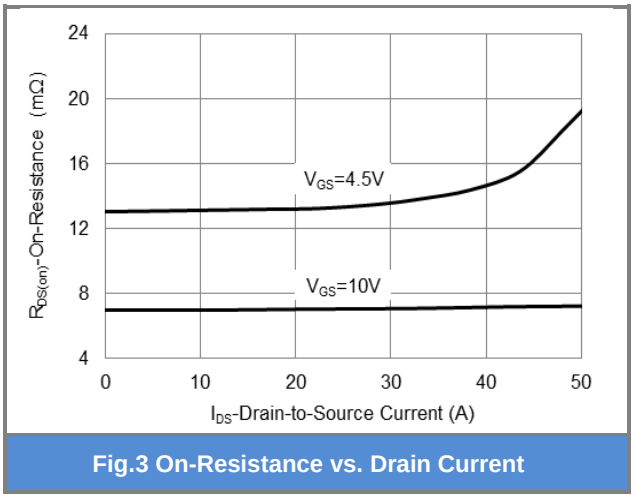

Fig.3 On-Resistance vs. Drain Current

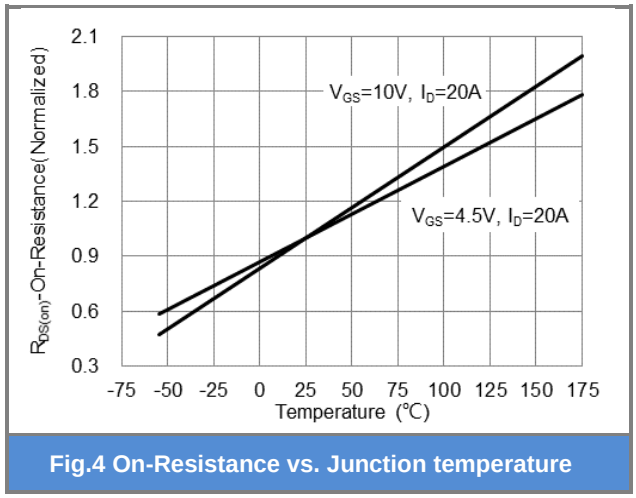

Fig.4 On-Resistance vs. Junction temperature

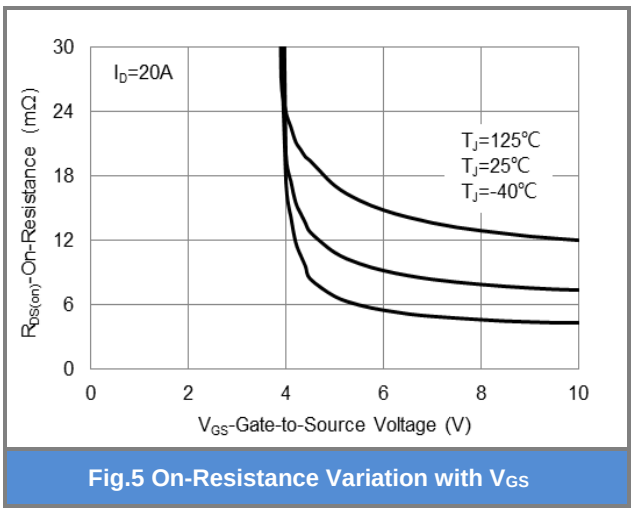

Fig.5 On-Resistance Variation with V_{GS}

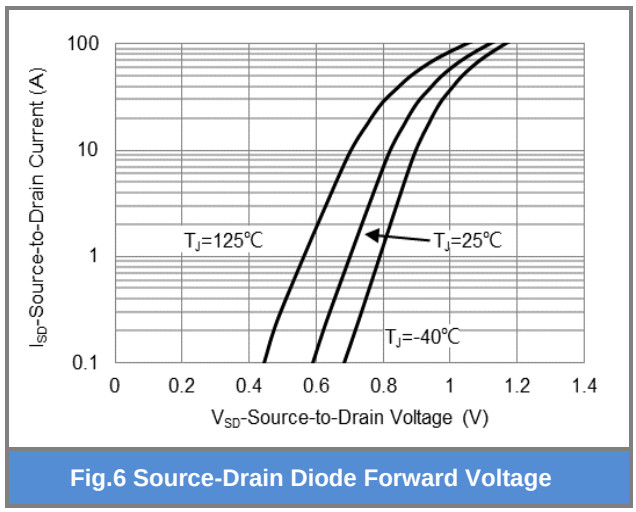

Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

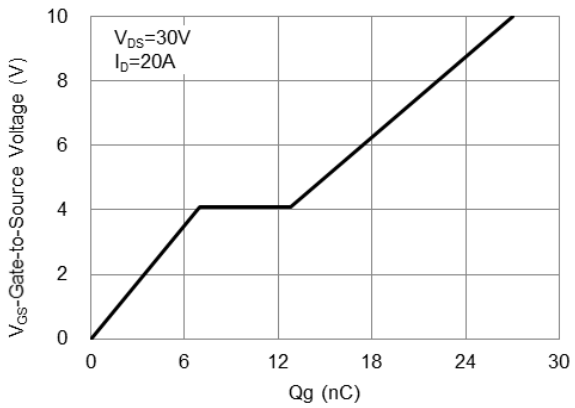

Fig.7 Gate-Charge Characteristics

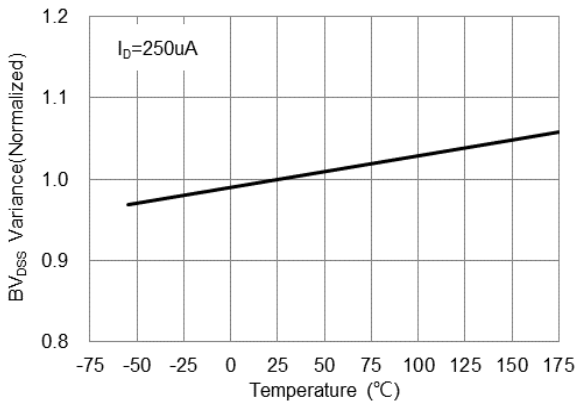

Fig.8 Breakdown Voltage Variation vs. Temperature

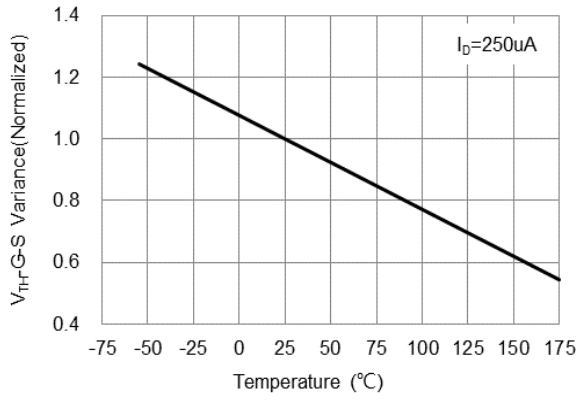

Fig.9 Threshold Voltage Variation with Temperature

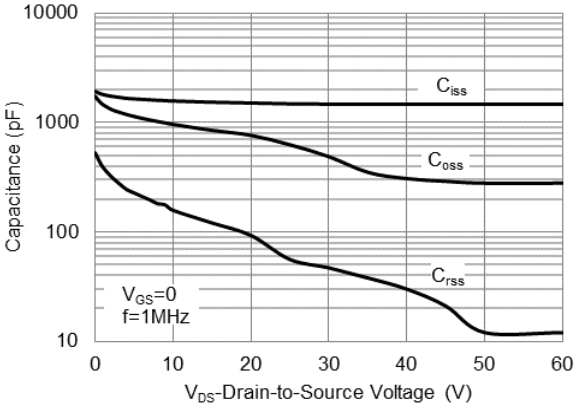

Fig.10 Capacitance vs. Drain-Source Voltage

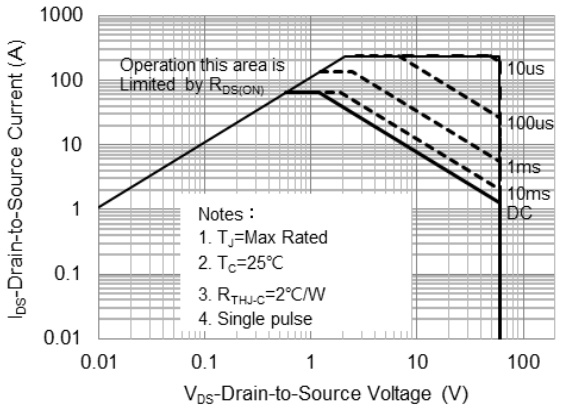

Fig.11 Maximum Safe Operating Area

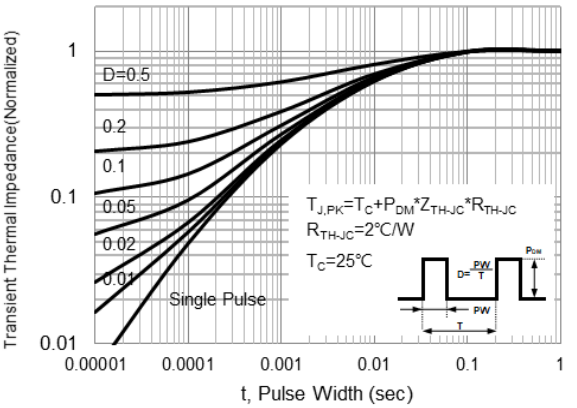

Fig.12 Normalized Transient Thermal Impedance

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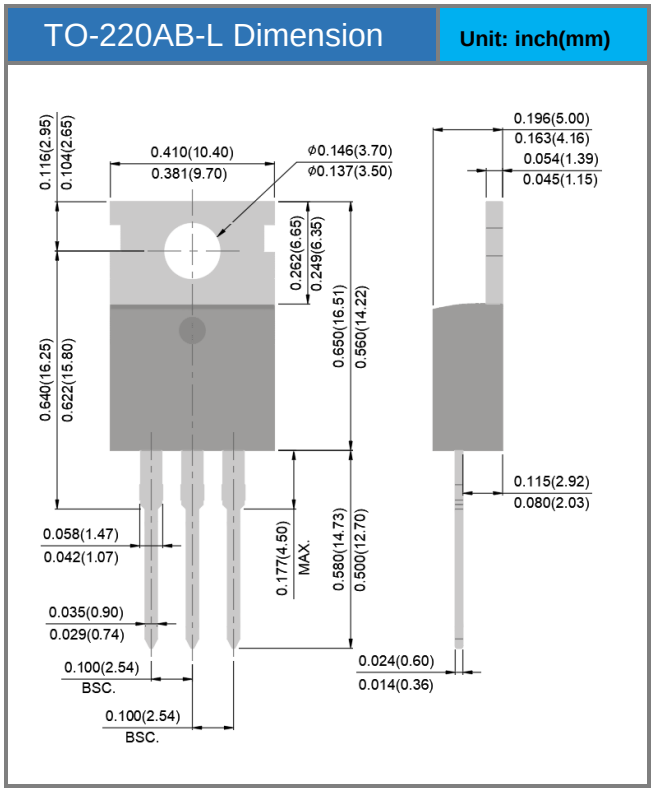
Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJP75N06SA-AU	TO-220AB-L	50 pcs / Tube	75N06SA

Packaging Information



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